TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

TA8159FN

1.5V Stereo Headphone Amplifier

The TA8159FN developed for play-back stereo headphone equipments (1.5V use). It is built in dual auto-reverse pre amplifiers, dual OCL power amplifiers, and a ripple filter.

Features

Power amp. Stage

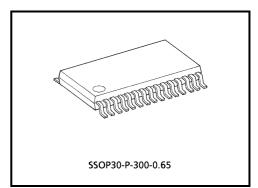
- OCL (output condenser-less)
- Low noise: $V_{no} = 48\mu V_{rms}$ (typ.)
- Output power: Po = 6mW (typ.) (at V_{CC} = 1.5V, f = 1kHz, THD = 10%)
- Excellent ripple rejection ratio: RR = 54dB (typ.)
- Voltage gain: G_V = 28dB (typ.)
- Built-in power amplifier mute.

Pre-amp. Stage

- Auto-reverse with F / R control switch
- Low noise: $V_{ni} = 1.7 \mu V_{rms}$ (typ.)
- Input coupling condenser-less
- Built-in input capacitor for reducing buzz noise
- Built-in pre-amplifier mute

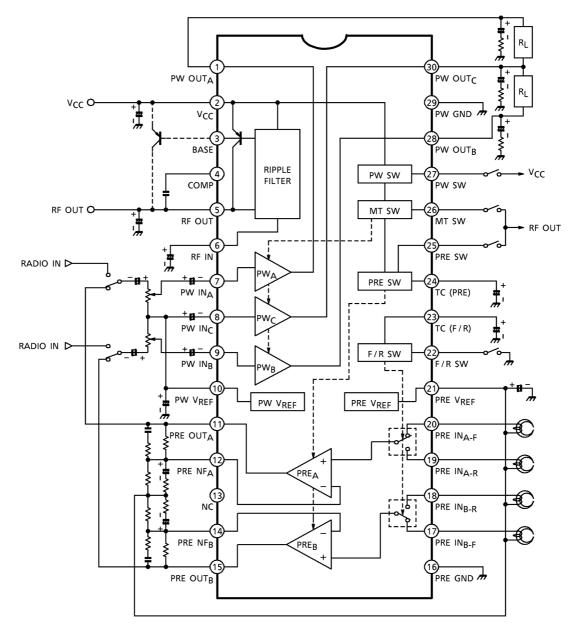
Total

- Built-in ripple filter
- Built-in power switch
- Operating supply voltage range: VCC (opr) = 0.9V~2.2V (Ta = 25°C)



Weight: 0.17g (typ.)

Block Diagram



Terminal Explanation Terminal Voltage: Typical Terminal Voltage at no Signal with Test Circuit. (V_{CC} = 1.2V, Ta = 25°C)

Terminal		Function	Internal Circuit	Terminal	
No.	Name			Voltage (V)	
1	PW OUT _A	 Output of power amplifier. 	7	0.6	
28	PW OUT _B				
30	PW OUT _C	Output of common power amplifier.	PW VREF 1kΩ GYZL 8	0.6	
7	PW IN _A			0.75	
9	PW IN _B		PW V _{REF}		
8	PW IN _C	Input of common power amplifier.		0.75	
2	V _{CC}	_	V _{CC} RF OUT	1.2	
3	BASE	Base bias of an external PNP transistor for fipple filter.		0.5	
4	COMP	Phase compensation of ripple filter circuit.		0.5	
5	RF OUT	Ripple filter output. Ripple filter circuit supplies V _{REF} circuit, pre–amplifier circuit, and F / R switch circuit with power source.		1.13	
6	RF IN	Ripple filter terminal.		1.13	
10	PW V _{REF}	Reference voltage of power amplifier.		0.75	

Terminal		Function	Internal Circuit	Terminal	
No.	Name		internal Orbuit	Voltage (V)	
11	PRE OUT _A	Output of pre-amplifier.		0.5	
15	PRE OUT _B		۲ <u>ــــــــــــــــــــــــــــــــــــ</u>		
12	PRE NFA	NF of pre-amplifier.		0.75	
14	PRE NF _B				
17	PRE IN _{B-F}	Forward input of pre-amplifier. (at F / R SW: OPEN)		0.75	
20	PRE IN _{A-F}				
18	PRE IN _{B-R}	Reverse input of pre–amplifier. (at F / R SW: GND)		0.75	
19	PRE IN _{A-R}		€)-#		
13	NC	_	_	_	
16	PRE GND	—	—	0	
21	PRE V _{REF}	Reference voltage of pre- amplifier.		0.75	
22	F/RSW	Forward / reverse mode switch. (OPEN: Forward mode GND: Reverse mode)	FF OUT → VCC → FF OUT → CC → FF OUT → CC → FF OUT	_	
23	TC (F / R)	Smoothing terminal. In order to reduce a pop noise at F / R switching.		0.7	
24	TC (PRE)	Smoothing terminal. In order to reduce a pop noise at pre–amplifier on / off switching.		0.7	
25	PRE SW	Pre–amplifier on / off switch. (RF out: ON GND / OPEN: OFF)		_	

<u>TOSHIBA</u>

Terminal		Function	Internal Circuit	Terminal	
No.	Name			Voltage (V)	
26	MT SW	Muting switch for power amplifier. (RF OUT: Mute OFF GND / OPEN: Mute ON)		_	
27	PW SW	Power on / off switch. (V _{CC} : ON GND / OPEN: OFF)		_	
29	PW GND	—	_	0	

Maximum Ratings (Ta = 25°C)

Characteris	tic	Symbol	Rating	Unit
Supply voltage		V _{CC}	3	V
Output current	Power	I _{o (peak)}	60	mA
Output current	Ripple filter	I _{RF}	5	ШA
Power dissipation	(Note)	PD	550	mW
Operating temperature		T _{opr}	T _{opr} –25~75	
Storage temperature		T _{stg}	-55~150	°C

(Note): Derated above Ta = 25° C in the proportion of 4.4mW / $^{\circ}$ C

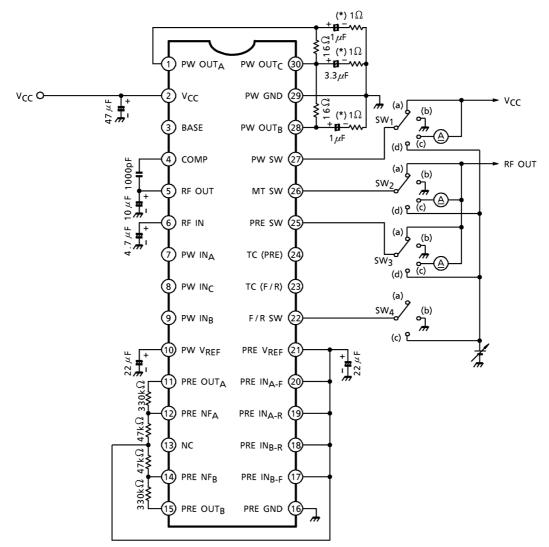
Electrical Characteristics

Unless Otherwise Specified: $V_{CC} = 1.2V$, f = 1kHz, Ta = 25°C, SW₁: a, SW₂: a, SW₃: a, SW₇: On Power–amplifier stage: R_g = 600 Ω , R_L = 16 Ω , SW₃: b, SW₆: a Pre–amplifier stage: R_g = 2.2k Ω , R_L = 10k Ω , SW₂: b, SW₅: a

Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit	
Quiescent current		I _{CCQ1}		Power OFF, SW ₁ : b, SW ₂ : b	_	0.1	5	μA	
		I _{CCQ2}	1	Power amp. OFF, SW2: b	_	2.8	4.5		
		I _{CCQ3}		V _{in} = 0	_	13	16	mA	
je	Voltage gain	GV		V _o = -22dBV	26	28	30	dB	
Power-amplifier stage	Channel balance	СВ			_	0	1.5	uБ	
	Output power	Po	2	V _{CC} = 1.5V, V _{in (A)} = V _{in} (B) THD = 10%	5	6	_	mW	
	Total harmonic distortion	THD ₁		V _{CC} = 1V, P _{o (A)} = P _{o (B)} = 1mW	_	0.4	1.5	%	
	Output noise voltage	V _{no}		BPF: 20Hz~20kHz, SW ₆ : b	_	48	70	μV _{rms}	

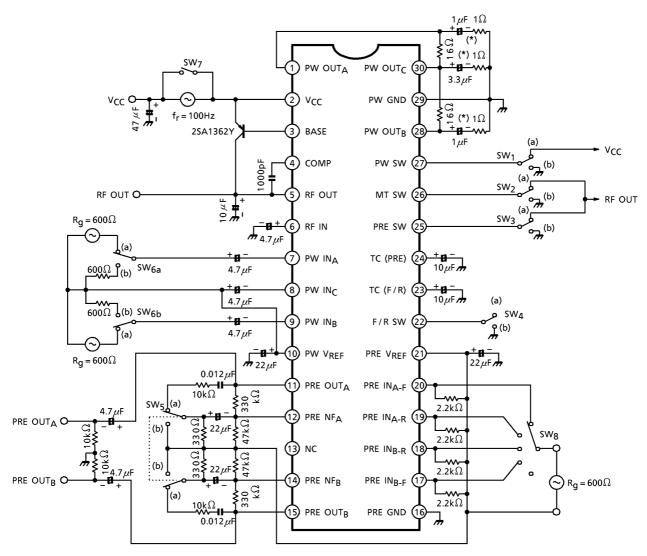
Characteristic		Symbol	Test Cir– cuit	Те	Test Condition		Тур.	Max.	Unit	
Power-amplifier stage	Ripple rejection ratio	RR ₁		32dBV	= 100Hz, V _r = – 5: b, SW7: OPEN	45	54			
	Cross talk (CH–A / CH–B)	CT ₁	2	V _o = -22dBV	V _o = -22dBV		38		dB	
	Power muting attenuation	ATT ₁		V _o = -22dBV	$V_0 = -22 dBV, SW_2: a \rightarrow b$ 70		83	-		
ge	Output voltage	V _{RF}		V _{CC} = 1V, I _R	_{RF} = 0	0.88	0.92		V	
Ripple filter stage	Ripple rejection ratio	RR ₂	2	V _{CC} = 1V, f _r = 100Hz, V _r = – 32dBV I _{RF} = 30mA, SW ₇ : OPEN		38	45	_	dB	
	Open loop voltage gain	G _{VO}		V _o = -22dBV	V _o = –22dBV, SW ₅ : b		70	_	dD	
	Closed loop voltage gain	G _{VC}		V _o = -22dBV		_	34	_	dB	
ge	Maximum output voltage	V _{om}		THD = 1%		160	290	_	mV _{rms}	
ifier sat	Total harmonic distortion	THD ₂	2	V_{CC} = 1V, V_0 = 100m V_{rms}		_	0.06	0.3	%	
Pre-amplifier satge	Equivalent input noise voltage	V _{ni}		BPF: 20Hz~20kHz, SW ₈ : OPEN NAB (f = 1kHz, G _V = 34dB)		_	1.7	2.7	μV _{rms}	
	Cross talk (CH–A / CH–B)	CT ₂					61	_		
	Cross talk (Forward / reverse)	CT ₃		$V_0 = -22 dBV$		_	61	_	dB	
	Pre muting attenuation	ATT ₂		V _o = –22dBV, SW ₃ : a→b		_	75	_		
Pov	ver on current	I ₂₇			V ₁₀ ≥ 0.5V, SW ₁ : c	5	—	_	μA	
Pov	ver off voltage	V ₂₇			$V_{10} \le 0.3V, SW_1: d$	0	—	0.3	V	
Pov curr	ver amp. Mute off rent	I ₂₆			V ₃₀ ≥ 0.4V, SW ₂ : c	5	_	_	μA	
Pov volt	ver amp. Mute on age	V ₂₆	1	V _{CC} = 0.9V	V ₃₀ ≤ 0.3V, SW ₂ : d	0	_	0.3	V	
Pre	. Amp. On current	I ₂₅			V ₂₄ ≥ 0.5V, SW ₃ : c	5	—	_	μA	
Pre	. Amp. Off voltage	V ₂₅			V ₂₄ ≤ 0.3V, SW ₃ : d	0	—	0.3	V	
Rev	verse mode voltage	V ₂₂			V ₂₃ ≥ 0.5V, SW ₄ : c	0	—	0.3	V	

Test Circuit 1



(*) Tantal condenser

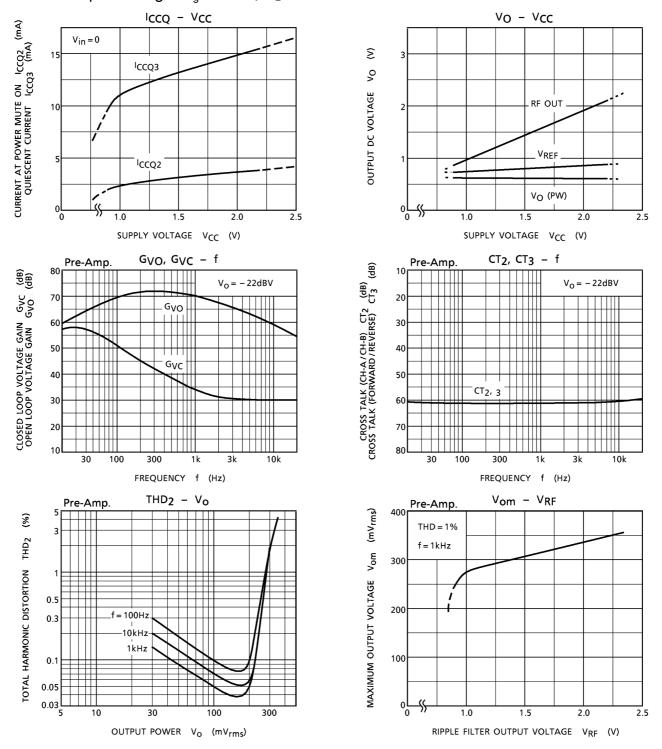
Test Circuit 2



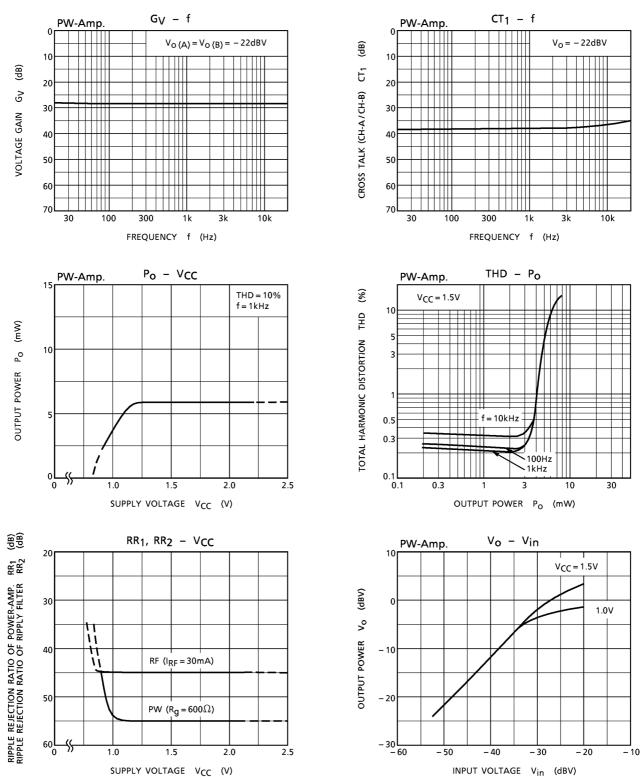
(*) Tantal condenser

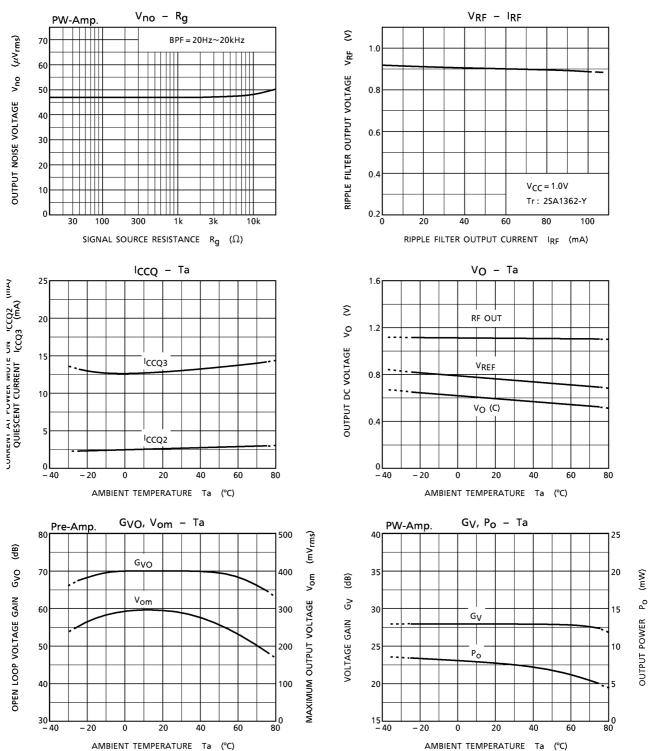
Characteristic Curves

Unless Otherwise Specified: V_{CC} = 1.2V, Ta = 25°C, f = 1kHz Pre–amplifier Stage: R_g = 2.2k Ω , R_L = 10k Ω Power Amplifier Stage: R_g = 600 Ω , R_L = 16 Ω

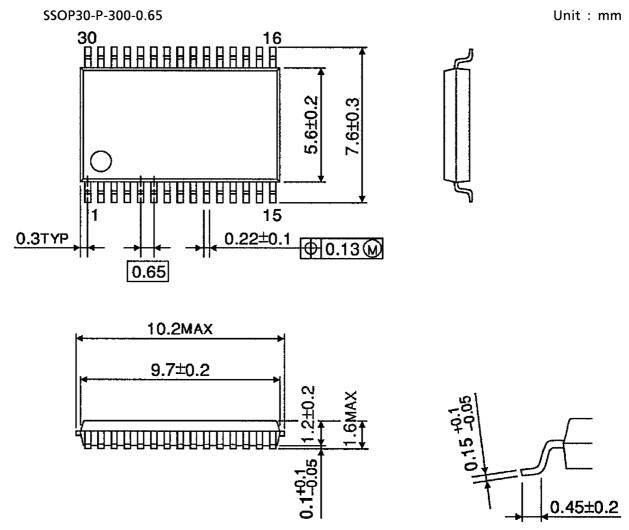








Package Dimensions



Weight: 0.17g (typ.)

RESTRICTIONS ON PRODUCT USE

000707EBA

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.